

INVERTER GRADE THYRISTORS

Stud Version

Features

- All diffused design
- Center amplifying gate
- Guaranteed high dv/dt
- Guaranteed high di/dt
- High surge current capability
- Low thermal impedance
- High speed performance

85A

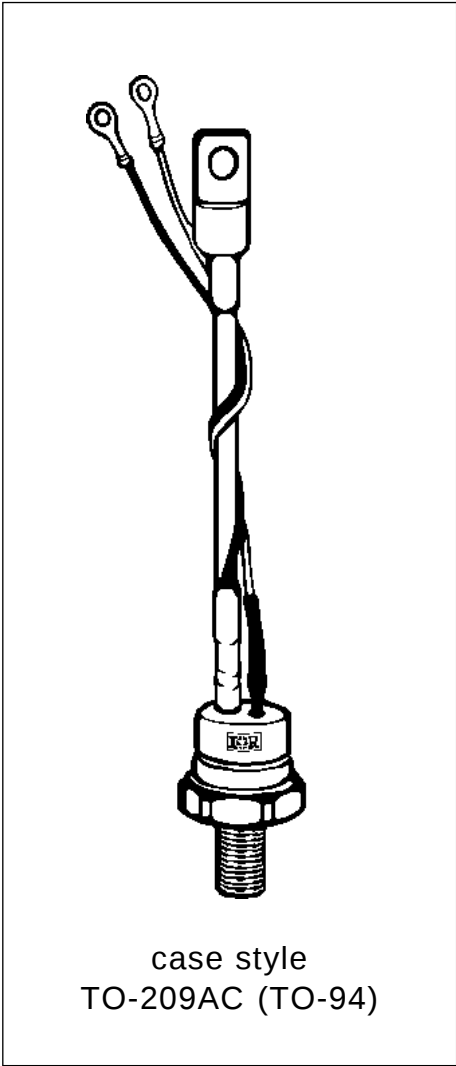
Typical Applications

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

Major Ratings and Characteristics

Parameters	ST083S	Units
$I_{T(AV)}$	85	A
@ T_C	85	°C
$I_{T(RMS)}$	135	A
I_{TSM} @ 50Hz	2450	A
@ 60Hz	2560	A
I^2t @ 50Hz	30	KA ² s
@ 60Hz	27	KA ² s
V_{DRM}/V_{RRM}	400 to 1200	V
t_q range (*)	10 to 30	μs
T_J	- 40 to 125	°C

(*) t_q = 10 to 20μs for 400 to 800V devices
 t_q = 15 to 30μs for 1000 to 1200V devices



case style
TO-209AC (TO-94)

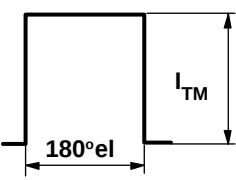
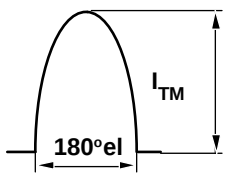
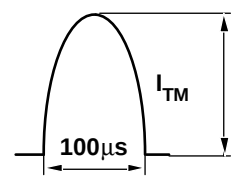
ST083S Series

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , maximum repetitive peak voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_j = T_j$ max. mA
ST083S	04	400	500	30
	08	800	900	
	10	1000	1100	
	12	1200	1300	

Current Carrying Capability

Frequency							Units
50Hz	210	120	330	270	2540	1930	A
400Hz	200	120	350	210	1190	810	
1000Hz	150	80	320	190	630	400	
2500Hz	70	25	220	85	250	100	
Recovery voltage Vr	50	50	50	50	50	50	V
Voltage before turn-on Vd	V _{DRM}		V _{DRM}		V _{DRM}		
Rise of on-state current di/dt	50	50	-	-	-	-	A/µs
Case temperature	60	85	60	85	60	85	°C
Equivalent values for RC circuit	22Ω / 0.15µF		22Ω / 0.15µF		22Ω / 0.15µF		

On-state Conduction

Parameter		ST083S	Units	Conditions		
I _{T(AV)}	Max. average on-state current @ Case temperature	85	A	180° conduction, half sine wave		
		85	°C			
I _{T(RMS)}	Max. RMS on-state current	135	A	DC @ 77°C case temperature		
I _{TSM}	Max. peak, one half cycle, non-repetitive surge current	2450		t = 10ms	No voltage	Sinusoidal half wave, Initial T _j = T _j max
		2560		t = 8.3ms	reapplied	
		2060		t = 10ms	100% V _{RRM}	
		2160		t = 8.3ms	reapplied	
² t	Maximum I ² t for fusing	30	KA ² s	t = 10ms	No voltage	
		27		t = 8.3ms	reapplied	
		21		t = 10ms	100% V _{RRM}	
		19		t = 8.3ms	reapplied	
I ² √t	Maximum I ² √t for fusing	300	KA ² √s	t = 0.1 to 10ms, no voltage reapplied		

On-state Conduction

Parameter	ST083S	Units	Conditions
V_{TM} Max. peak on-state voltage	2.15	V	$I_{TM} = 300A$, $T_J = T_J \text{ max}$, $t_p = 10\text{ms}$ sine wave pulse
$V_{T(TO)1}$ Low level value of threshold voltage	1.46		$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$.
$V_{T(TO)2}$ High level value of threshold voltage	1.52		$(I > \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$.
r_{t1} Low level value of forward slope resistance	2.32	m Ω	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$.
r_{t2} High level value of forward slope resistance	2.34		$(I > \pi \times I_{T(AV)})$, $T_J = T_J \text{ max}$.
I_H Maximum holding current	600	mA	$T_J = 25^\circ\text{C}$, $I_T > 30A$
I_L Typical latching current	1000		$T_J = 25^\circ\text{C}$, $V_A = 12V$, $R_a = 6\Omega$, $I_G = 1A$

Switching

Parameter	ST083S	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/ μs	$T_J = T_J \text{ max}$, $V_{DRM} = \text{rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$
t_d Typical delay time	0.80	μs	$T_J = 25^\circ\text{C}$, $V_{DM} = \text{rated } V_{DRM}$, $I_{TM} = 50A$ DC, $t_p = 1\mu\text{s}$ Resistive load, Gate pulse: 10V, 5 Ω source
t_q Max. turn-off time (*)	Min 10 Max 30		$T_J = T_J \text{ max}$, $I_{TM} = 100A$, commutating $di/dt = 10A/\mu\text{s}$ $V_R = 50V$, $t_p = 200\mu\text{s}$, dv/dt : see table in device code

(*) $t_q = 10$ to $20\mu\text{s}$ for 400 to 800V devices; $t_q = 15$ to $30\mu\text{s}$ for 1000 to 1200V devices.

Blocking

Parameter	ST083S	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μs	$T_J = T_J \text{ max}$., linear to 80% V_{DRM} , higher value available on request
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	30	mA	$T_J = T_J \text{ max}$, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST083S	Units	Conditions
P_{GM} Maximum peak gate power	40	W	$T_J = T_J \text{ max}$, $f = 50\text{Hz}$, $d\% = 50$
$P_{G(AV)}$ Maximum average gate power	5		
I_{GM} Max. peak positive gate current	5	A	$T_J = T_J \text{ max}$, $t_p \leq 5\text{ms}$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J \text{ max}$, $t_p \leq 5\text{ms}$
$-V_{GM}$ Maximum peak negative gate voltage	5		
I_{GT} Max. DC gate current required to trigger	200	mA	$T_J = 25^\circ\text{C}$, $V_A = 12V$, $R_a = 6\Omega$
V_{GT} Max. DC gate voltage required to trigger	3	V	
I_{GD} Max. DC gate current not to trigger	20	mA	$T_J = T_J \text{ max}$, rated V_{DRM} applied
V_{GD} Max. DC gate voltage not to trigger	0.25	V	

ST083S Series

Thermal and Mechanical Specifications

Parameter	ST083S	Units	Conditions
T _J Max. junction operating temperature range	-40 to 125	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJC} Max. thermal resistance, junction to case	0.195	K/W	DC operation
R _{thCS} Max. thermal resistance, case to heatsink	0.08		Mounting surface, smooth, flat and greased
T Mounting torque, ± 10%	15.5 (137)	Nm (lbf-in)	Non lubricated threads
	14 (120)	Nm (lbf-in)	Lubricated threads
wt Approximate weight	130	g	
Case style	TO-209AC (TO-94)		See Outline Table

ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.034	0.025	K/W	T _J = T _J max.
120°	0.041	0.042		
90°	0.052	0.056		
60°	0.076	0.079		
30°	0.126	0.127		

Ordering Information Table

Device Code

ST083S12PFK0

1

2

3

4

5

6

7

8

9

10

1

 - Thyristor

2

 - Essential part number

3

 - 3 = Fast turn off

4

 - S = Compression bonding Stud

5

 - Voltage code: Code x 100 = V_{RRM} (See Voltage Ratings Table)

6

 - P = Stud Base 1/2" 20UNF

7

 - Reapplied dv/dt code (for t_q Test Condition)

8

 - t_q code

9

 - 0 = Eyelet terminals (Gate and Aux. Cathode Leads)
1 = Fast-on terminals (Gate and Aux. Cathode Leads)
2 = Flag terminals (For Cathode and Gate Terminals)

10

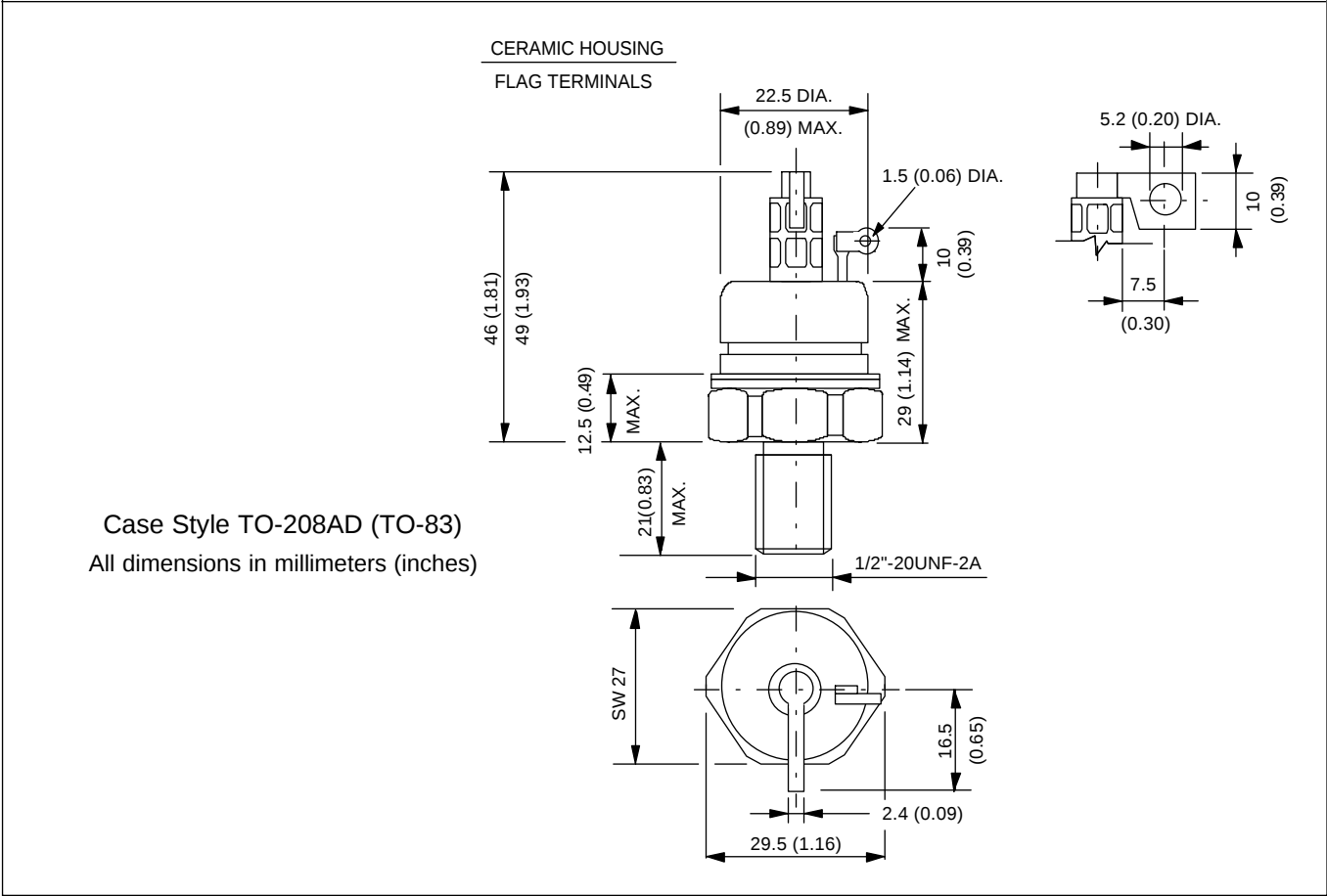
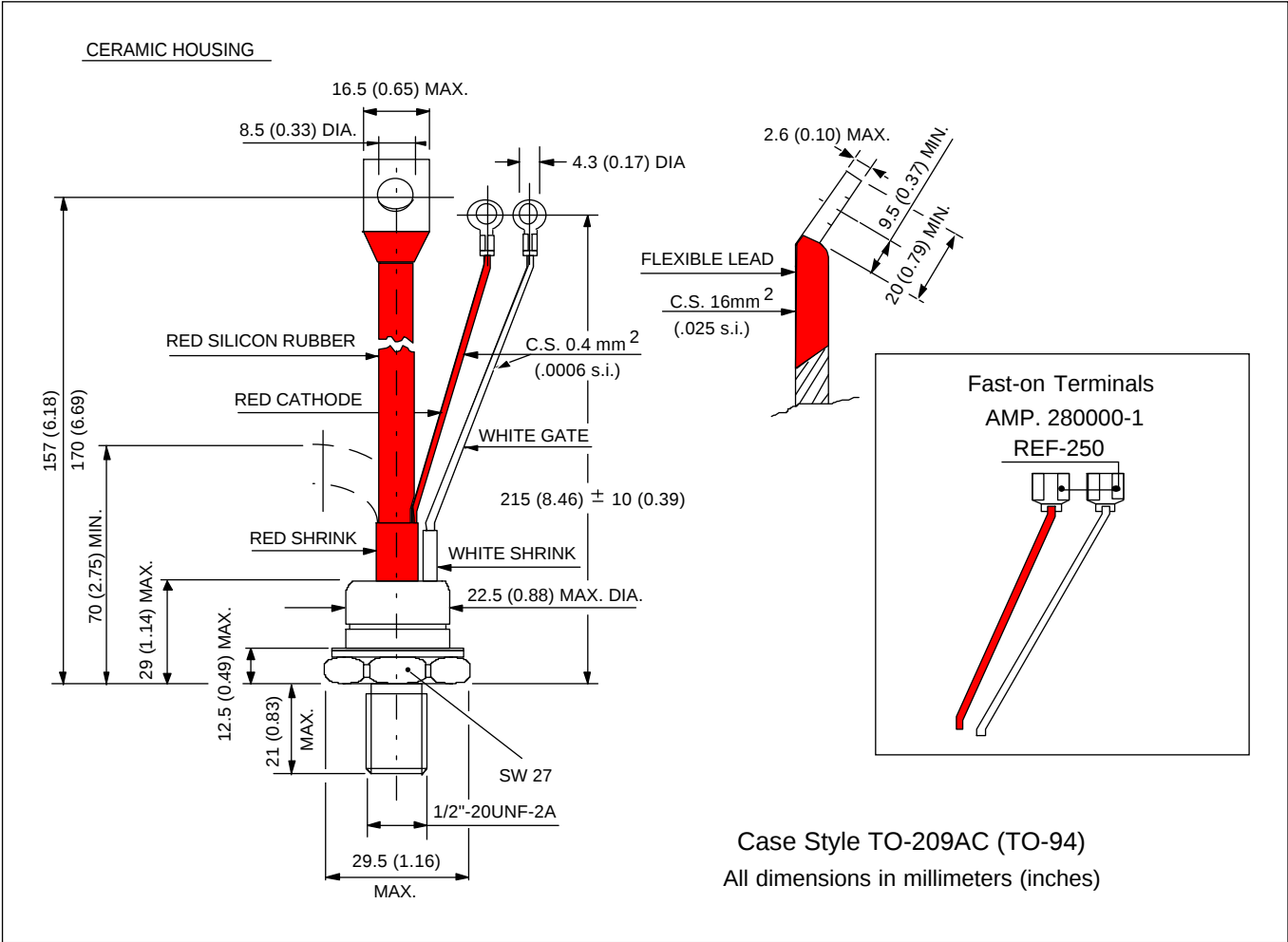
 - Critical dv/dt:
None = 500V/μsec (Standard value)
L = 1000V/μsec (Special selection)

dv/dt - t _q combinations available						
dv/dt (V/μs)		20	50	100	200	400
t _q (μs)	10	CN	DN	EN	FN *	HN
	12	CM	DM	EM	FM *	HM
	15	CL	DL	EL	FL	HL
	18	CP	DP	EP	FP *	HP
	20	CK	DK	EK	FK *	HK
t _q (μs)	15	CL	--	--	--	--
	18	CP	DP	EP	FP *	--
	20	CK	DK	EK	FK *	HK
	25	CJ	DJ	EJ	FJ	HJ
	30	--	DH	EH	FH	HH

*Standard part number.

All other types available only on request.

Outline Table



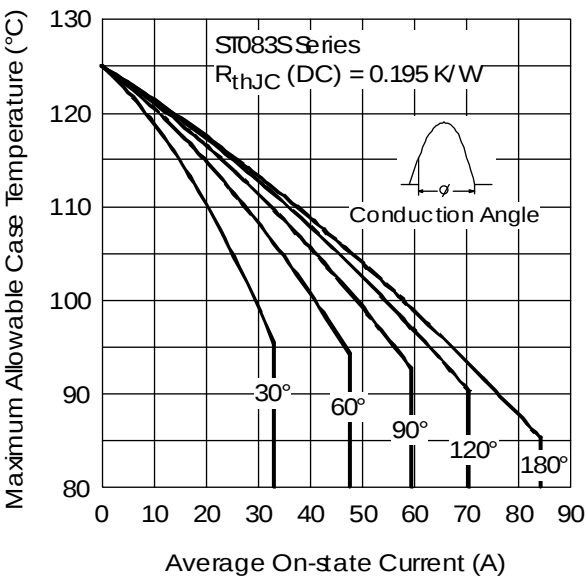


Fig. 1 - Current Ratings Characteristics

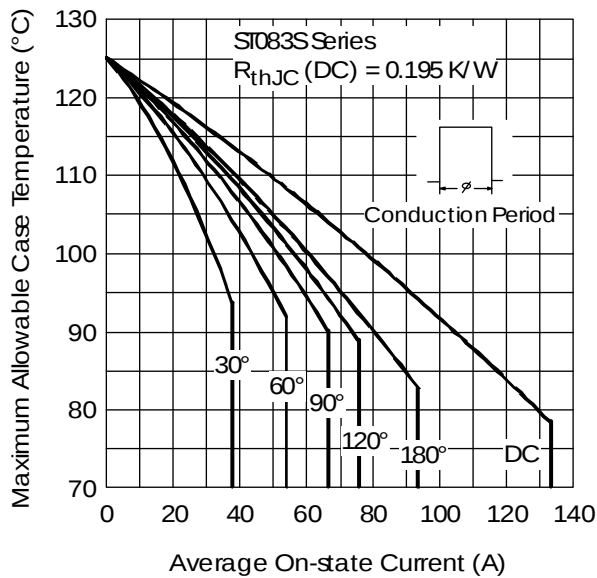


Fig. 2 - Current Ratings Characteristics

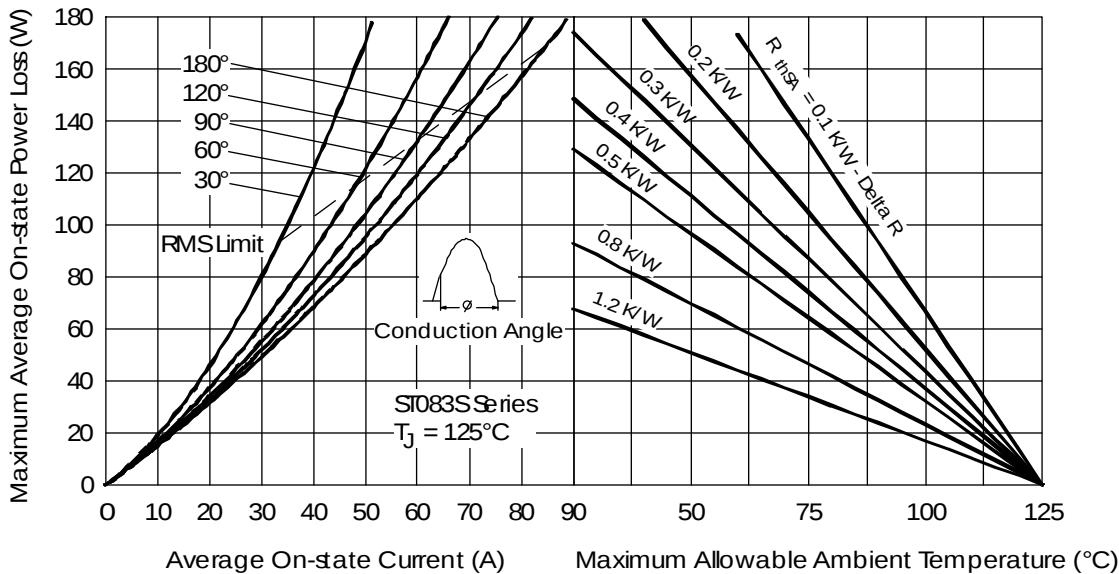


Fig. 3 - On-state Power Loss Characteristics

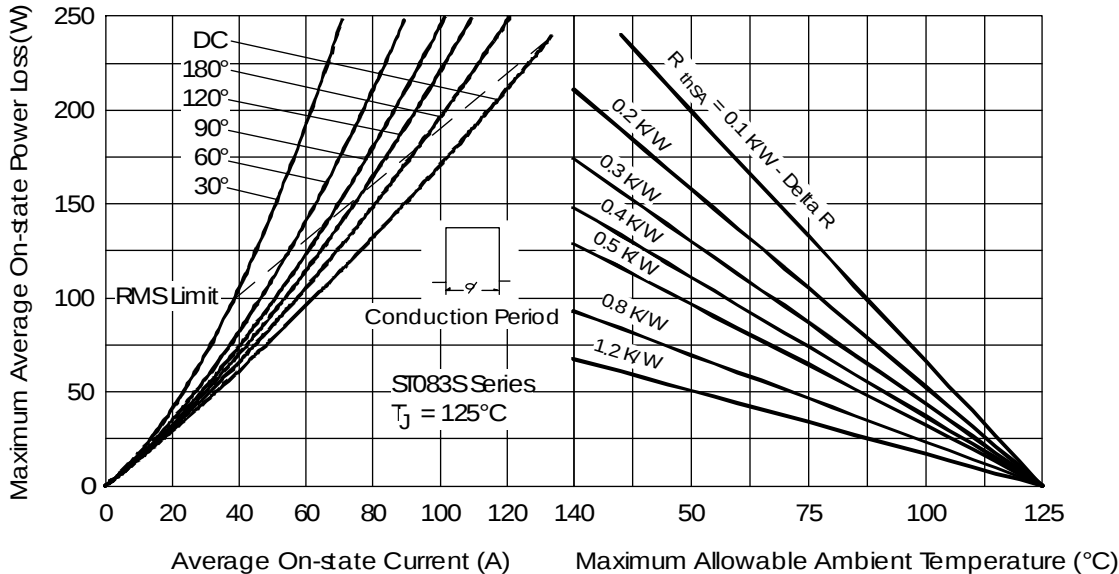


Fig. 4 - On-state Power Loss Characteristics

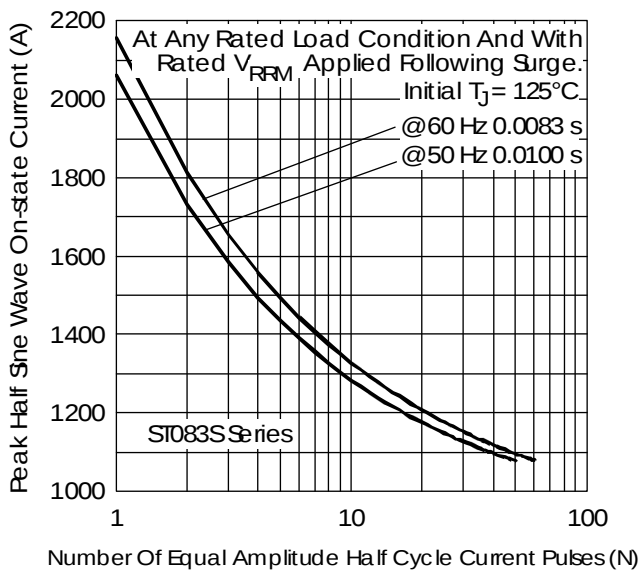


Fig. 5 - Maximum Non-repetitive Surge Current

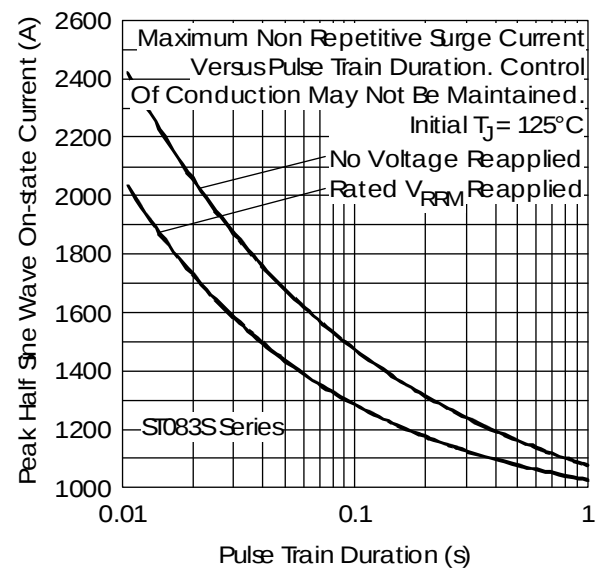


Fig. 6 - Maximum Non-repetitive Surge Current

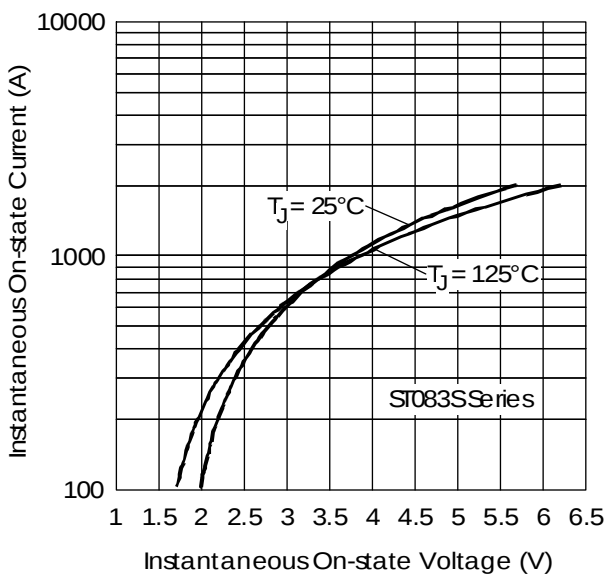


Fig. 7 - On-state Voltage Drop Characteristics

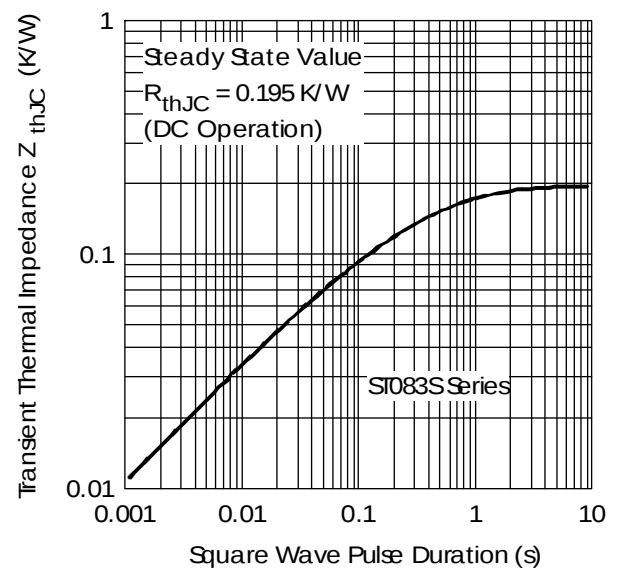


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

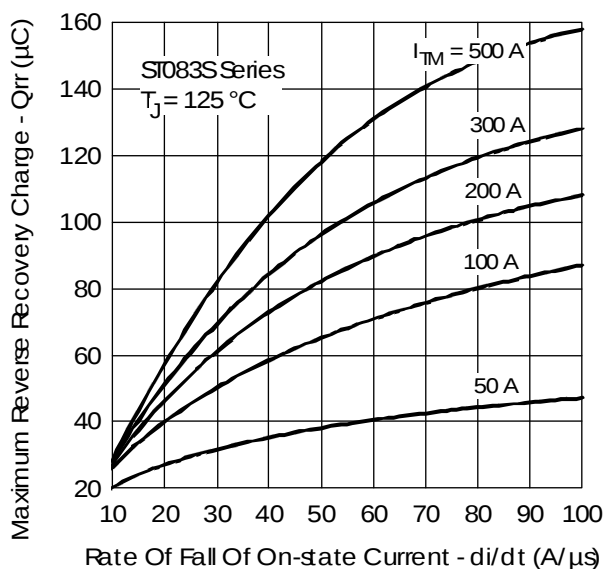


Fig. 9 - Reverse Recovered Charge Characteristics

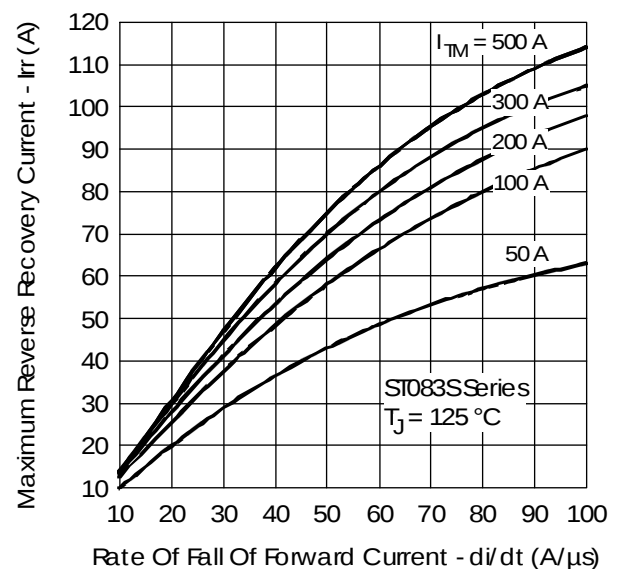


Fig. 10 - Reverse Recovery Current Characteristics

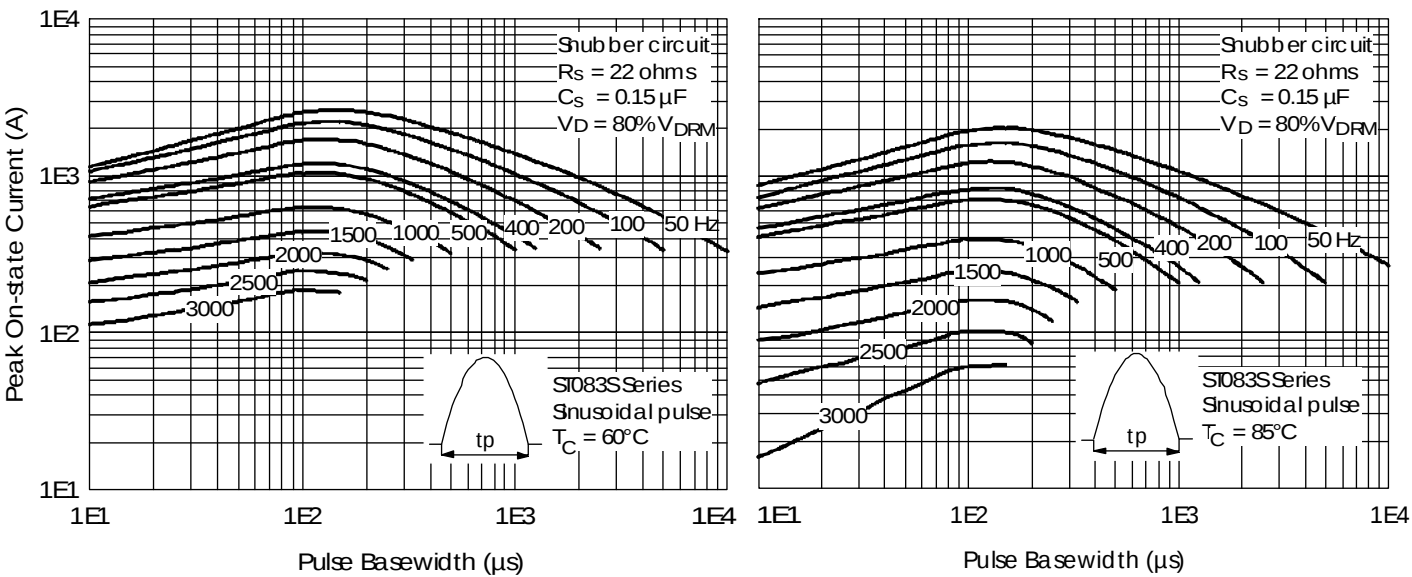


Fig. 11 - Frequency Characteristics

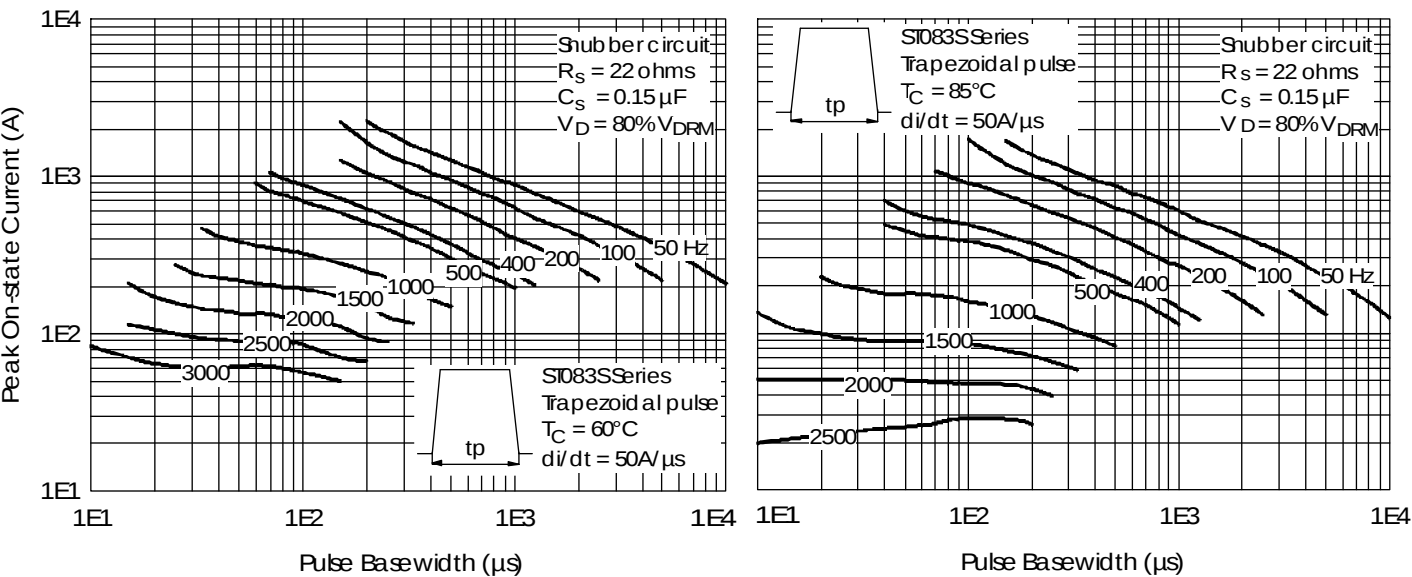


Fig. 12 - Frequency Characteristics

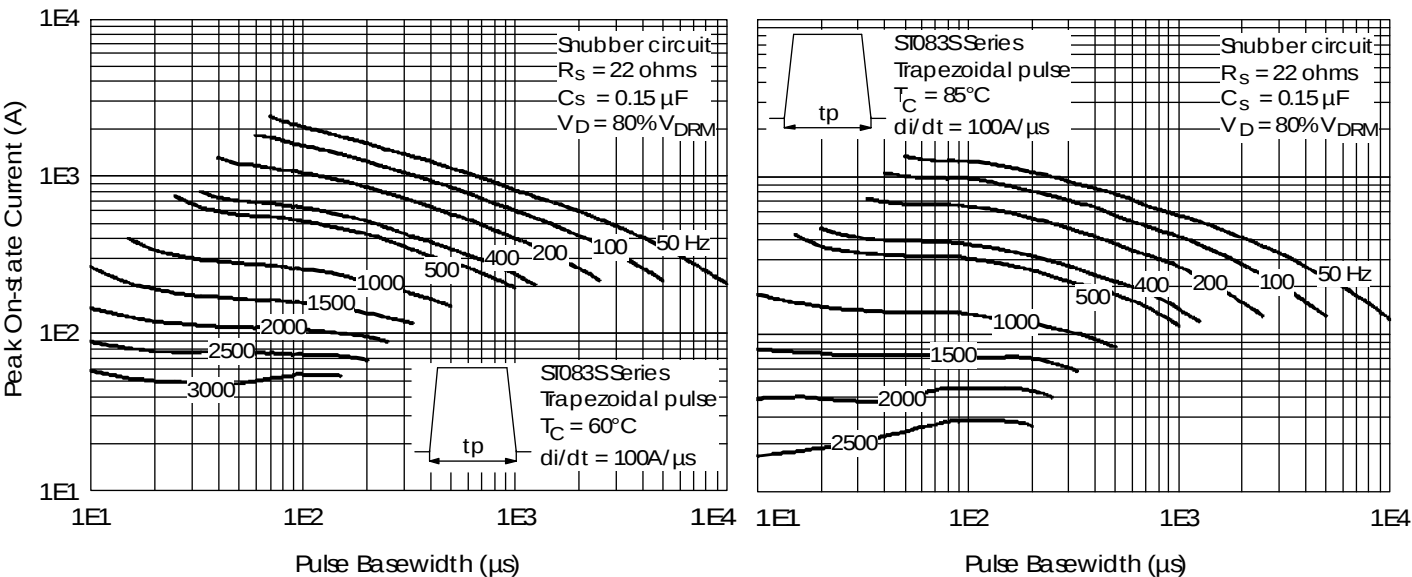


Fig. 13 - Frequency Characteristics

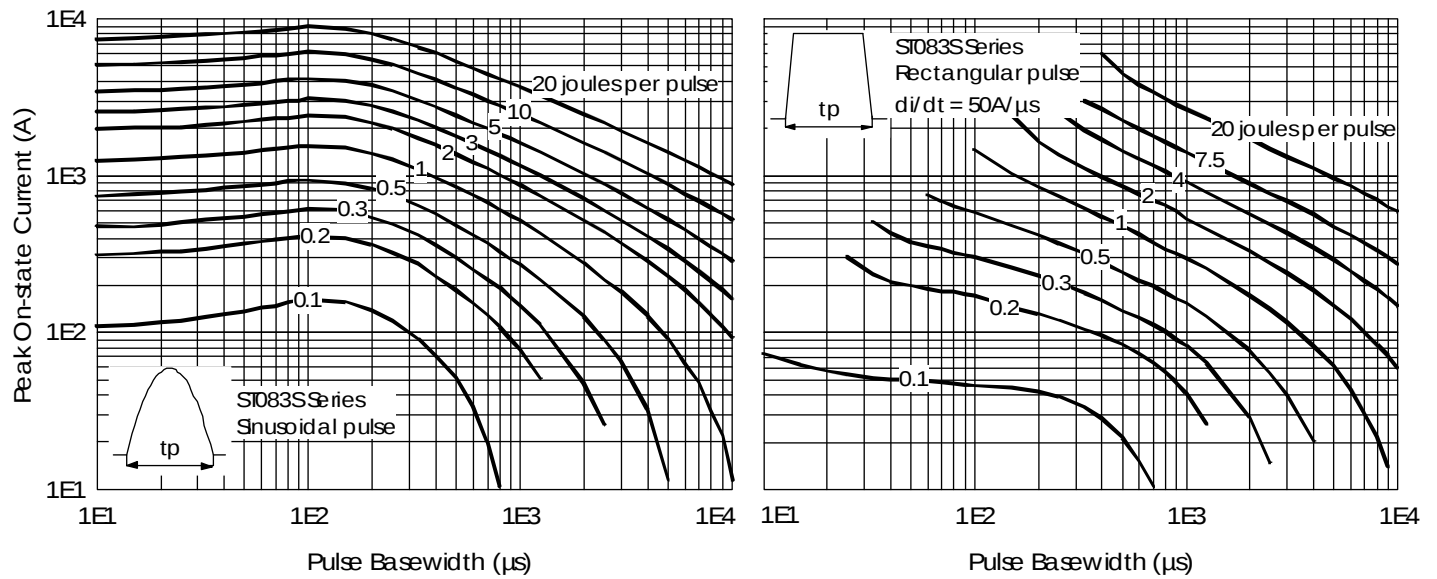


Fig. 14 - Maximum On-state Energy Power Loss Characteristics

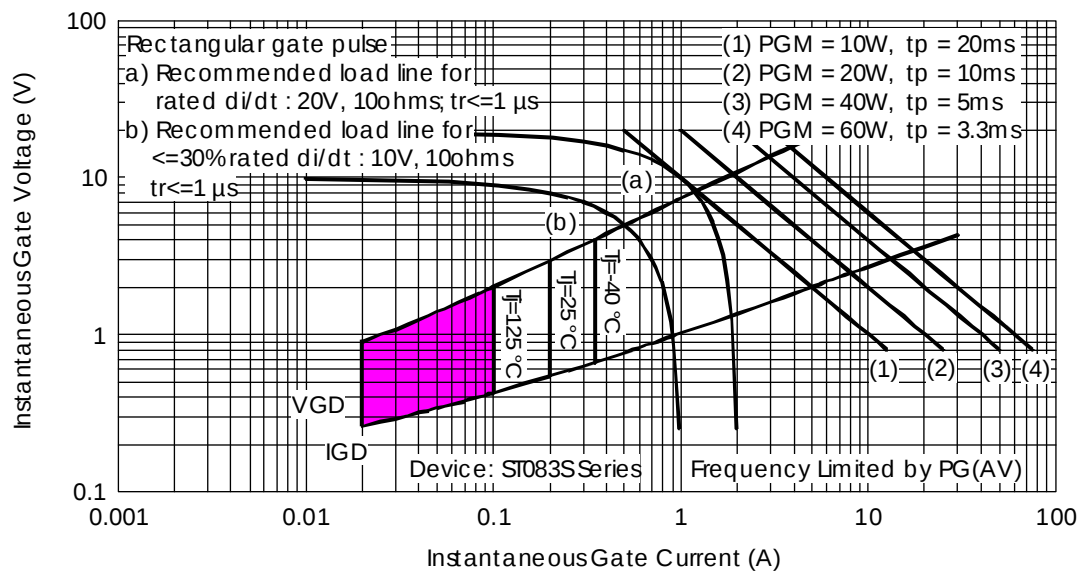


Fig. 15 - Gate Characteristics